

## IGBT

Low  $V_{CE(sat)}$  IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

## IKW30N65EL5

650V DuoPack IGBT and diode  
Low  $V_{CE(sat)}$  series fifth generation

Data sheet

Low  $V_{CE(sat)}$  series fifth generation

## Low $V_{CE(sat)}$ IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

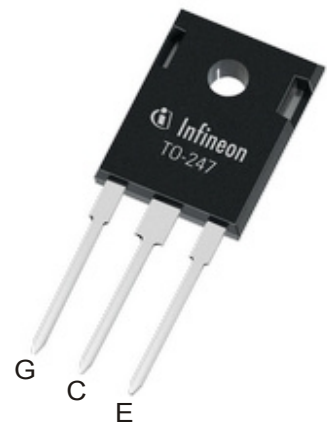
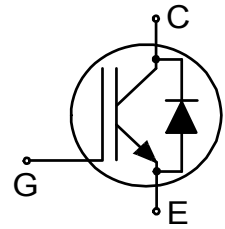
### Features and Benefits:

Low  $V_{CE(sat)}$  L5 technology offering

- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Best-in-Class tradeoff between conduction and switching losses
- 650V breakdown voltage
- Low gate charge  $Q_G$
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating
- RoHS compliant
- Complete product spectrum and PSpice models:  
<http://www.infineon.com/igbt/>

### Applications:

- Uninterruptible power supplies
- Solar photovoltaic inverters
- Welding machines



### Key Performance and Package Parameters

| Type        | $V_{CE}$ | $I_C$ | $V_{CEsat}, T_{vj}=25^{\circ}C$ | $T_{vjmax}$ | Marking | Package    |
|-------------|----------|-------|---------------------------------|-------------|---------|------------|
| IKW30N65EL5 | 650V     | 30A   | 1.05V                           | 175°C       | K30EEL5 | PG-TO247-3 |